Foundry Process Data Sheet



PPH25

0.25µm power pHEMT

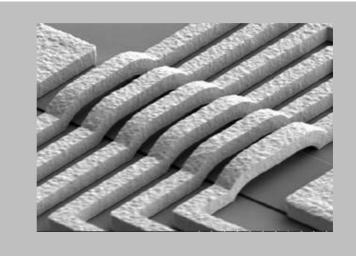
Description

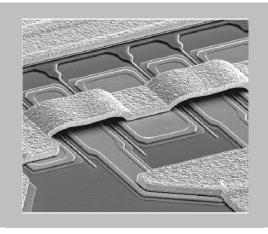
The 0.25µm pHEMT process is optimized for power and multipurpose up to 40GHz. The process includes two metal interconnect layers, precision TaN resistors, high values TiWSi resistors, MIM capacitors, air-bridges and via-holes through the substrate.

Overcoating layer is available as an option.

Main Features

- 0.25µm pHEMT process
- Typical Ft: 50GHz
- TaN and TiWSi resistors
- GaAs resistors
- M.I.M. capacitors
- Air bridges
- Via-holes
- Operation Vds= 6V
- Wafer thickness: 100µm
- Wafer diameter: 100mm





Design Kit Characteristics

- Available for ADS from Keysight and MwO from AWR
- DRC on line with ADS DK
- Schematic entry with autolayout generation
- Scalable models for passive devices
- Scalable non-linear models for FET
- Scalable models for series and parallel switch configuration
- Data for spread analysis

Electrical Characteristics

ELEMENT / Parameters	Min	Тур	Max	Units	Conditions
FET/					
Threshold voltage Vp	-1.2	-0.9	-0.7	V	Vds=2.5V,lds=ldss/100
Transconductance Gm	370	430	-	mS/mm	Vds=2.5V, Vgs=0V
Saturation current ldss	250	325	400	mA/mm	Vds=2.5V, Vgs=0V
Breakdown voltage Vbds	12	13	-	V	Ids= Idss/100
Coplanar FET (2x75µm) equivalent circuit					
Transconductance Gme	50	60	75	mS	Vds=3.0V, Vgs=0V
Input capacitance Cin	140	170	200	fF	Vds=3.0V, Vgs=0V
Feedback capacitance Cf	9	12	15	fF	Vds=3.0V, Vgs=0V
Output resistance Rout	550	750	950	Ω	Vds=3.0V, Vgs=0V
TaN RESISTOR /					
sheet resistance	26	30	34	Ω/square	
MIM CAPACITOR /					
density	220	250	280	pF/mm2	@1MHz
TiWSi RESISTOR /					
sheet resistance	800	1000	1200	Ω/square	
GaAs RESISTOR					
Ohmic contact resistance	-	0.15	0.3	$\Omega.mm$	
GaAs sheet resistance	85	95	105	Ω/square	

Ordering Information

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